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BLAKELY SOKOLOFF TAYLOR & ZAFMAN
12400 WILSHIRE BOULEVARD
SEVENTH FLOOR
LOS ANGELES, CA 90025-1030

EXAMINER

MATTHEW, AARON D

ART UNIT PAPER NUMBER

2114

DATE MAILED: 10/18/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/056,393

Applicant(s)

VENKATRAMAN ET AL.

Examiner

Aaron D Matthew

Art Unit

2114

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 24 January 2002.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-30 is/are pending in the application.
- 4a) Of the above claim(s) 29 and 30 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-28 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☒ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 24 January 2002 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

Election/Restrictions

1. Applicant's election with traverse of group I (claims 1-28), in the reply filed on 09/20/2004 is acknowledged. The traversal is on the ground(s) that, "all groups of restricted claims are properly presented in the application, undue diverse searching should not be required, and all claims should be examined together." This is not found persuasive because the examiner has already shown that diverse searching would be required in examining both groups, I and II.

The requirement is still deemed proper and is therefore made FINAL.

Specification

2. The disclosure is objected to because of the following informalities:
 - Element 102 is improperly labeled, "integrated circuit 102", in the description referring to Fig. 2, on page 10, line 33 and page 11, line 13. This should be changed to read, "reconfigurable memory 102".
 - On page 18, lines 4-5, the enable bit of Fig. 7 is improperly labeled, "enable bit 604". This should be changed to read, "enable bit 704".
 - On page 19, lines 7, memory block 212 is improperly labeled, memory block 2121.

Appropriate correction is required.

Claim Objections

3. Claims 1-28 have been examined.
4. Claims 12 and 20 are objected to because of the following informalities: both claims are improperly listed as "(Currently Amended)". The claim language has not been amended in either claim, and, therefore, both claims should be indicated as, "(Original)". Appropriate correction is required.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

5. Claim 10 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 10 recites the limitation "the corresponding size of addressable space of the memory block" in line 5. There is insufficient antecedent basis for this limitation in the claim. The examiner suggests changing the claim language to read, "the corresponding size of addressable space of the one or more memory blocks."

Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

6. Claims 1, 3-5, and 9-13 are rejected under 35 U.S.C. 102(e) as being anticipated by Hoskins, (US 2001/0042223 A1).

Regarding claim 1, Hoskins teaches a method comprising:

- Testing a memory to determine a location of a bad memory cell, (see par. 0015, lines 4-7: discovering a defective memory cell inherently requires some means of testing said cell);
- Mapping out an address location associated with the bad memory cell, (note par. 0009, lines 1-4; wherein mapping defective sectors to a good sector is considered synonymous with mapping out the defective sector); and

- Offsetting one or more physical address locations associated with one or more good memory cells so that logical addressing is linear and the memory appears contiguous, (see par. 0058, lines 5-9, and note Fig. 8).

Regarding claims 3 and 9, Hoskins teaches a method, as disclosed in reference to claim 1, wherein:

- The memory is organized into one or more clusters, each of the one of more clusters having one or more memory blocks, (see par. 0042, lines 1-6, wherein the memory is divided into a set of tracks {clusters} each comprising a number of sectors, and note par. 0003 wherein a sector is a memory block comprising memory cells);
- One or more bad memory cells are located within one or more respective memory blocks, (it is inherent, in determining that one or more memory blocks are defective, note par. 0015, that said memory blocks contain one or more bad memory cells); and
- Mapping out of the address location associated with the bad memory cell includes mapping out one or more respective memory blocks, (sectors), having the one or more bad memory cells, (note, again, par. 0058, lines 5-9, and note Fig. 8, wherein a sector having a bad memory cell is mapped out).

Regarding claims 4 and 5, again note Fig. 8, wherein offsetting one or more physical address locations associated with the one or more good memory cells is by one

memory block, (sector), and thus, the corresponding size of addressable space of said memory block having the bad memory cell. Note also that each of the one or more good memory cells, shown addressable in ascending order after the memory block having the bad memory cell, has its one or more physical address locations offset, (signified by the corresponding logical address), by the size of addressable space in a memory block to linearize the logical addressing.

Regarding claim 10, note, again, Fig. 8, wherein offsetting the one or more physical address locations, (i.e. the slipping of the LBA, see par. 0058), associated with the one or more good memory cells is by one or more memory blocks, (sectors), associated with the number of one or more respective memory blocks having the one or more bad memory cells and the corresponding size of addressable space of the one or more memory blocks, (the size of addressable space of a sector disclosed as 512 bytes, see par. 0003, the sector itself being addressable).

Regarding claim 11, Hoskins teaches a reconfigurable memory comprising:

- An array of data sectors, each comprising an array of memory cells, (see par. 0003);
- A reconfigurable memory controller, (see par. 0048), to receive a logical address and generate a physical address to address the array of memory cells, the reconfigurable memory controller to map out one or more physical addresses of words, (sectors), having one or more bad memory cells, (a

defective sector, comprising an array of memory cells, inherently comprises one or more defective memory cells), to form a linear logical address space without addresses to words of the one or more bad memory cells, (see par. 0058 and Fig. 8).

Regarding claim 12, see par. 0042, lines 1-6, wherein the memory is divided into one or more tracks, (clusters), each comprising one or more sectors, and note par. 0003 wherein a sector is a memory block comprising an array of memory cells.

Regarding claim 13, see Fig. 8, and note that the sectors, as described in Hoskins, can be interpreted both as words and as memory blocks each comprising an array of memory cells.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

7. Claims 2 and 14-28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hoskins as applied to claims 11-13 above, and further in view of Sugibayashi, (U.S. 5,848,021).

Regarding claim 2, Hoskins fails to teach that the memory, discussed in reference to claim 1, is within an integrated circuit and the testing is self-testing performed on chip by a built in self tester.

Sugibayashi teaches a method of reconfiguring a partially defective memory wherein the memory is within an integrated circuit and the testing is self-testing performed on chip by a built in self tester, (see col. 10, lines 19-28, and Fig. 5, element 23d).

Sugibayashi and Hoskins are analogous art because they are from the same field of endeavor, viz., reconfigurable computer memory devices.

At the time of applicant's invention, one of ordinary skill in the art would have considered it obvious to combine the teachings in order to achieve a method of reconfiguring a partially defective memory within the integrated circuit of Sugibayashi, that utilizes the advantages taught in Hoskins in creating a linear logical address space in a partially defective memory and the advantages of Sugibayashi in using on chip self testing to determine the defective locations in the memory.

One of ordinary skill in the art would have been motivated to combine the teachings because the integrated circuit of Sugibayashi meets an implicit need in the art of

memory devices, by improving memory access speeds. One of ordinary skill in the art would have clearly recognized that the use of magnetic disk drives and semiconductor memory devices is prevalent in the art, and that both devices are direct substitutes in most applications, (note Sugibayashi, col. 1, lines 16-20). Moreover, Hoskins and Sugibayashi both disclose a need for techniques to reconfigure partially defective memory, and one of ordinary skill in the art would have clearly recognized that techniques for remapping defective memory cells, as disclosed in Hoskins, are directly applicable to the partially defective semiconductor memory of Sugibayashi. Therefore, one of ordinary skill in the art would have clearly recognized the substitutability of a semiconductor memory device for the disk drive of Hoskins, and would have been motivated to utilize the integrated circuit comprising said reconfigurable semiconductor memory device to improve memory access speeds. The on-chip, self-testing of Sugibayashi offers further motivation to combine the teachings by reducing the time and costs involved in testing semiconductor memory devices during manufacture.

Regarding claim 14, Hoskins fails to teach that the reconfigurable memory controller includes a configuration register associated with each memory block, each configuration register including a memory block enable bit, the memory block enable bit to map out the respective memory blocks having the bad memory cells.

However, Hoskins does teach maintaining a reserve sector on the disk drive,

associated with each memory block, used to store and retrieve information required for the disc drive controller to manage and control the storage and retrieval of information in the disc drive, (see par. 0050).

Sugibayashi teaches a semiconductor memory device used to map out defective memory blocks, wherein a reconfigurable memory controller, (see Fig. 3, 7d), includes a configuration register including a memory block enable bit, the memory block enable bit to map out the respective memory blocks having the bad memory cells, (see col. 4, lines 17-30; the plurality of memory units and memory cell groups corresponding to configuration registers and memory blocks respectively; also note col. 7, lines 34-51 wherein the control data information is a memory block enable bit).

At the time of applicant's invention, one of ordinary skill in the art would have considered it obvious to combine the teachings in order to achieve a reconfigurable memory controller in a semiconductor memory device, as disclosed in Sugibayashi, that utilizes the advantages taught in Hoskins in creating a linear logical address space in a partially defective memory device.

One of ordinary skill in the art would have been motivated to combine the teachings because the configuration registers, taught in Sugibayashi, meet a need in common with the reserve sectors of Hoskins, in providing the memory controller with

reconfiguration information, and offer a further advantage of improving access times for said information, (see Sugibayashi, col. 3, lines 52-58). One of ordinary skill in the art would have also clearly recognized that the use of magnetic disk drives and semiconductor memory devices is prevalent in the art, and that both devices are direct substitutes in most applications, (note Sugibayashi, col. 1, lines 16-20). Moreover, Hoskins and Sugibayashi both disclose a need for techniques to reconfigure partially defective memory, and one of ordinary skill in the art would have clearly recognized that techniques for remapping defective memory blocks, as disclosed in Hoskins, are directly applicable to the partially defective semiconductor memory of Sugibayashi. Therefore, one of ordinary skill in the art would have clearly recognized the substitutability of a semiconductor memory device for the disk drive of Hoskins, and would have been motivated to utilize the configuration registers disclosed in Sugibayashi in place of the reserve sectors of Hoskins to improve access times for the information stored therein.

Regarding claims 15-17, Sugibayashi teaches a reconfigurable memory, as discussed in reference to claim 14, wherein:

- Each configuration register further includes a base address associated with one or more upper address bits of an address to begin the physical addressing of a respective memory block having all good memory cells, (note col. 4 lines 35-40, wherein physical addressing of non-defective memory

blocks is assigned through the configuration registers, and note col. 6, lines 32-55, wherein this physical base address is associated with one or more upper address bits of an address);

- A value of the base address is compared with a value of the one or more upper address bits of the address to determine if each memory block having all good memory cells is selected for access, (note col. 4, lines 35-40, wherein a memory block is selectively enabled upon a successful comparison of the base address and said one or more upper address bits); and
- For a given memory block the comparison between the value of the base address and the value of the one or more upper address bits of the address results in a match and the given memory block is selected for access, (note col. 4, lines 55-58 wherein a logical address selects a given, non-defective memory block for access upon comparison with said base address).

Regarding claim 18, Sugibayashi teaches that each memory block is a self contained memory unit, (see Fig. 5), including an array of memory cells, (see col. 4, lines 17-21), an address decoder, (see Fig. 5, elements 22c and 22d), sense amplifier array, (see Fig. 5, element 21c), and tri-state bus drivers, (see col. 10, lines 45-50).

Regarding claim 19, Hoskins teaches, as has been shown in the discussion regarding claim 11, a reconfigurable memory comprising:

- An array of data sectors, each comprising an array of memory cells, (see par. 0003);
- A reconfigurable memory controller, (see par. 0048), to receive a logical address and generate a physical address to address the array of memory cells, the reconfigurable memory controller to map out physical addresses of words, (sectors), having bad memory cells, (a defective sector, comprising an array of memory cells, inherently comprises one or more defective memory cells), to form a linear logical address space without addresses to words of the bad memory cells, (see par. 0058 and Fig. 8).

Hoskins teaches a disc drive comprising said reconfigurable memory, but fails to teach an integrated circuit comprising said reconfigurable memory.

Sugibayashi teaches an integrated circuit comprising a reconfigurable memory for mapping out defective memory cells.

At the time of applicant's invention, one of ordinary skill in the art would have considered it obvious to combine the memory reconfiguration technique of Hoskins with the integrated circuit memory device of Sugibayashi in order to achieve an

integrated circuit comprising a reconfigurable semiconductor memory utilizing the memory reconfiguration techniques of Hoskins.

One of ordinary skill in the art would have been motivated to combine the teachings because the integrated circuit of Sugibayashi meets an implicit need in the art of memory devices, by improving memory access speeds. One of ordinary skill in the art would have clearly recognized that the use of magnetic disk drives and semiconductor memory devices is prevalent in the art, and that both devices are direct substitutes in most applications, (note Sugibayashi, col. 1, lines 16-20). Moreover, Hoskins and Sugibayashi both disclose a need for techniques to reconfigure partially defective memory, and one of ordinary skill in the art would have clearly recognized that techniques for remapping defective memory blocks, as disclosed in Hoskins, are directly applicable to the partially defective semiconductor memory of Sugibayashi. Therefore, one of ordinary skill in the art would have clearly recognized the substitutability of a semiconductor memory device for the disk drive of Hoskins, and would have been motivated to utilize the integrated circuit comprising said reconfigurable semiconductor memory device to improve memory access speeds.

Regarding claim 20, see Hoskins, par. 0042, lines 1-6, wherein the memory is divided into one or more tracks, (clusters), each comprising one or more sectors,

and note par. 0003 wherein a sector is a memory block comprising an array of memory cells.

Regarding claim 21, see Hoskins, Fig. 8, and note that the sectors, as described in Hoskins, can be interpreted both as words and as memory blocks each comprising an array of memory cells.

Regarding claim 22, Sugibayashi teaches a reconfigurable memory controller, (see Fig. 3, 7d), that includes a configuration register associated with each of the one or more memory blocks, each configuration register including a memory block enable bit, the memory block enable bit to map out the respective memory blocks having the bad memory cells, (see col. 4, lines 17-30; the plurality of memory units and memory cell groups corresponding to configuration registers and memory blocks respectively; also note col. 7, lines 34-51 wherein the control data information is a memory block enable bit). Please also refer to the arguments presented regarding claim 14.

Regarding claim 23, see Hoskins, par. 0048, wherein the reconfigurable memory controller includes a memory block base address, (note lines 5-7).

Regarding claim 24, note that the integrated circuit of Sugibayashi is operable specifically as a reconfigurable semiconductor memory device, (see Abstract), and, as such, is an application specific integrated circuit.

Regarding claims 25-28, Sugibayashi teaches that said integrated circuit further comprises:

- A host port, (see col. 10, lines 19-23 and note col. 9, lines 55-59 wherein the external device is disclosed as a host);
- A memory test register, (col. 12, line 8);
- A built-in memory self tester, (see "test circuit", col. 12, line 6 and Fig. 5, element 23d); and
- A test access port, (see col. 10, lines 23-28).

8. Claims 7 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hoskins, as applied to claim 1 above, and further in view of Lin et al, (U.S. 6,141,768).

Regarding claim 7, Hoskins fails to teach that testing the memory includes:

- Writing one or more test patterns into memory cells in the memory;

- Reading out data from the memory cells; and
- Comparing the read out data with an expected pattern of the one or more test patterns to determine a location of the bad memory cell.

However, Hoskins does teach identifying newly-defective sectors during operation of the disc drive, (see par. 0090), which inherently requires testing of the memory, and further discloses that error detection operations comprising writing to the memory cells, reading from the memory cells, and performing appropriate operations upon the retrieved data, (see par. 0041).

Lin teaches a self-corrective memory system which is reconfigurable upon detection of defective memory cells, and performs self testing upon the memory, including:

- Writing a test pattern into the memory cells; and
- Verifying the accuracy of the results, (see col. 1, lines 49-54), which inherently includes:
 - Reading out data from the memory cells; and
 - Comparing the read out data with an expected pattern to determine the location of the bad memory cell.

At the time of applicant's invention, one of ordinary skill in the art would have considered it obvious to combine the memory self-testing method of Lin, with the memory reconfiguration method of Hoskins in order to achieve a means of detecting defective memory cells which was not explicitly stated in Hoskins.

One of ordinary skill in the art would have been motivated to combine the teachings because Lin teaches a method of self-testing that was not explicitly stated in Hoskins, but meets an explicitly stated need in Hoskins of detecting defective memory cell locations. Hoskins teaches that error detection operations should be performed to locate defective memory locations, but fails to teach a specific means of performing said error detection. Therefore, one of ordinary skill in the art would have been motivated to use the method of Lin, (see col. 1, lines 49-50, in which Lin discloses said testing procedure as a "known testing procedure"), in order to enable the error detection needed in the memory reconfiguration method of Hoskins.

Regarding claim 8, see Hoskins, Fig. 8, wherein the location of a bad memory cell is associated with a "PCHS" address.

9. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Hoskins, as applied to claims 1 and 3 above, and further in view of Lo et al, (U.S. 4,922,451), and Beausoliel, (U.S. 3,735,368).

Hoskins fails to teach that the memory discussed in reference to claims 1 and 3 has four clusters each having four memory blocks and each memory block containing

512 kilobits of memory cells. However, Hoskins does teach that each memory device is to have a number of tracks, (clusters), appropriate to constraints of the medium hosting said tracks, (see Fig. 3), and each comprising a plurality of sectors with 512 bytes of memory cells.

Beausoliel teaches a reconfigurable memory device organized into four clusters each having four memory blocks, (see Fig. 1, elements 16 and 18 respectively).

Beausoliel teaches that each memory block contains 256 bits of memory cells, (see col. 4, lines 4-5), but fails to teach that each memory block contains 512 kilobits of memory cells.

Lo teaches a method for remapping partially defective memory wherein a memory comprises a plurality of memory blocks and each memory block contains 512 kilobits, (64 kilobytes), of memory cells, (see col. 4, lines 18-26).

Lo, Beausoliel and Hoskins are analogous art because they are from the same field of endeavor, viz., reconfiguring partially defective memory.

At the time of applicant's invention, one of ordinary skill in the art would have considered it obvious to combine the teachings of Beausoliel and Lo with the memory reconfiguration method of Hoskins in order to achieve a reconfigurable

memory comprised of four clusters each having four memory blocks, (as in Beausoliel), and each memory block containing 512 kilobits of memory cells, (as in Lo).

One of ordinary skill in the art would have been motivated to combine the teachings because Hoskins teaches that the number of tracks, (clusters), per memory, and sectors, (memory blocks), per track are often determined by one skilled in the art based on the constraints of the memory device, (note par. 0042). Therefore, in view of Beausoliel and Lo, one of ordinary skill in the art would have considered it obvious to partition a memory into four clusters with four memory blocks each containing 512 kilobits of memory cells, utilizing the methods of Hoskins, based upon a preference and the constraints of the memory device being used.

Conclusion

10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure:

- Sims, III et al, (U.S. 6,212,647 B1), teaches a system using logical addressing to slip defective data blocks, creating a logically linear address space.
- DeVoy et al, (U.S. 3,803,560), teaches reconfiguring a memory by removing memory modules and forming a continuous address space among the remaining functional modules.

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- Dobbek et al, (U.S. 5,937,435), teaches a method for reconfiguring a memory by skipping defective sectors in a disk drive.
- Wildenberg et al, (U.S. 6,295,595 B1), teaches a method for reconfiguring a partially defective memory by mapping out defective memory cells, enabling only functional partitions of the memory array.
- Logan, (U.S. 5,146,571), teaches a system utilizing a tree structure to create logical address to map around defective memory sectors and create a logically linear address space.
- Hodge et al, (U.S. 5,293,593), teaches a method and apparatus for the mapping of physically non-contiguous memory fragments to be linearly addressable.
- Takata et al, (U.S. 6,400,602 B2), teaches a method of reconfiguring a semiconductor memory device by mapping out defective memory blocks and creating a linear address space.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Aaron D Matthew whose telephone number is (571) 272-3662. The examiner can normally be reached on Mon-Fri, from 8:00 am - 5:30 pm.


If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert W Beausoliel can be reached on (571) 272-3645. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Aaron D Matthew
Examiner
Art Unit 2114

ADM


ROBERT BEAUSOLIEL
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2100